

## 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection in a DSN0603-2 (SOD962-2) leadless ultra small Chip-Scale Package (CSP).

## 2. Features and benefits

- Average forward current I<sub>F(AV)</sub> ≤ 0.5 A
- Reverse voltage V<sub>R</sub> ≤ 20 V
- Low forward voltage typ. V<sub>F</sub> = 245 mV
- Low reverse current typ.  $I_R = 5 \mu A$
- Package height typ. 0.3 mm

## 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Ultra high speed switching
- LED backlight for mobile application

## 4. Quick reference data

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
I <sub>F(AV)</sub>	average forward current	δ = 0.5; f = 20 kHz; T <sub>amb</sub> = 115 °C; square wave	[1]	-	-	0.5	A
		$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> = 145 °C; square wave		-	-	0.5	A
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>F</sub>	forward voltage	$I_F$ = 10 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C		-	245	310	mV
I <sub>R</sub>	reverse current	$V_R$ = 10 V; $T_j$ = 25 °C; pulsed		-	5	25	μA
t <sub>rr</sub>	reverse recovery time	$I_F$ = 500 mA; $I_R$ = 500 mA; $I_{R(meas)}$ = 100 mA; $T_j$ = 25 °C		-	1.9	-	ns





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## 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode[1]		1 🕂 2
2	А	anode		sym001
			Transparent top view	
			DSN0603-2 (SOD962-2)	

[1] The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering information								
Type number	Package							
	Name	Description	Version					
PMEG2005AESF	DSN0603-2	Leadless ultra small package; 2 terminals; body 0.6 x 0.3 x 0.3 mm	SOD962-2					

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG2005AESF	6

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	20	V
l <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 140 °C; δ = 1		-	0.71	А
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; T <sub>amb</sub> = 115 °C; square wave	[1]	-	0.5	A
		$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> = 145 °C; square wave		-	0.5	A
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$		-	2	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	4.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	405	mW
			[3]	-	660	mW
			[1]	-	1200	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

## 9. Thermal characteristics

#### Table 6.Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1][2]	-	-	310	K/W
	from junction to ambient		[1][3]	-	-	190	K/W
	ambient		[1][4]	-	-	105	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	40	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.

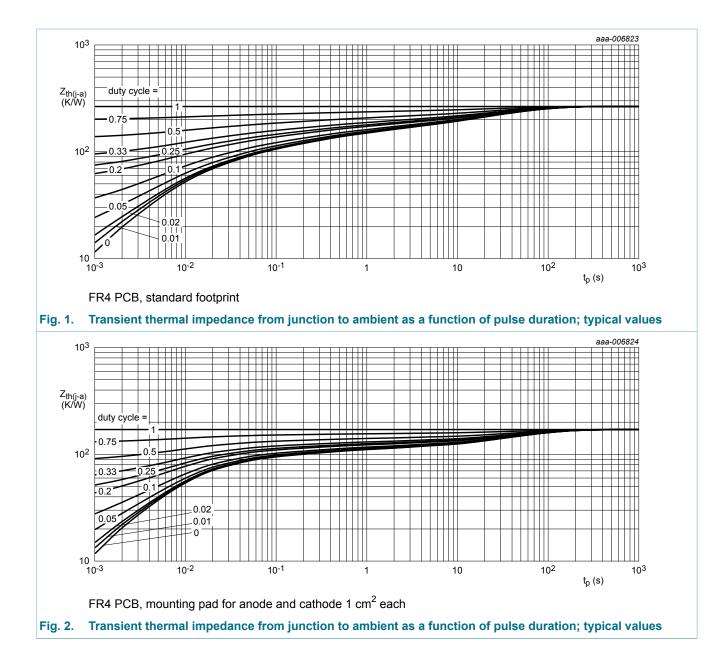
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for anode and cathode 1 cm<sup>2</sup> each.

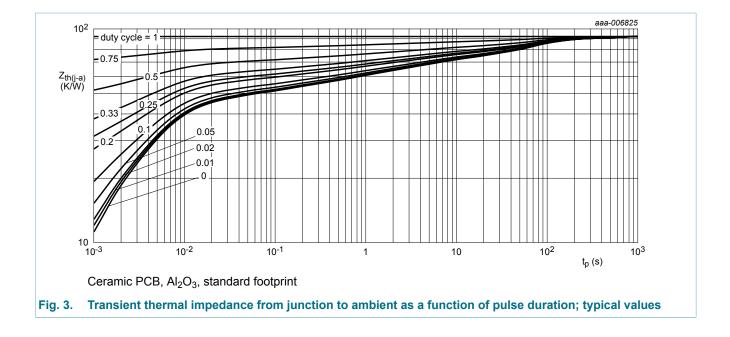
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of anode tab.

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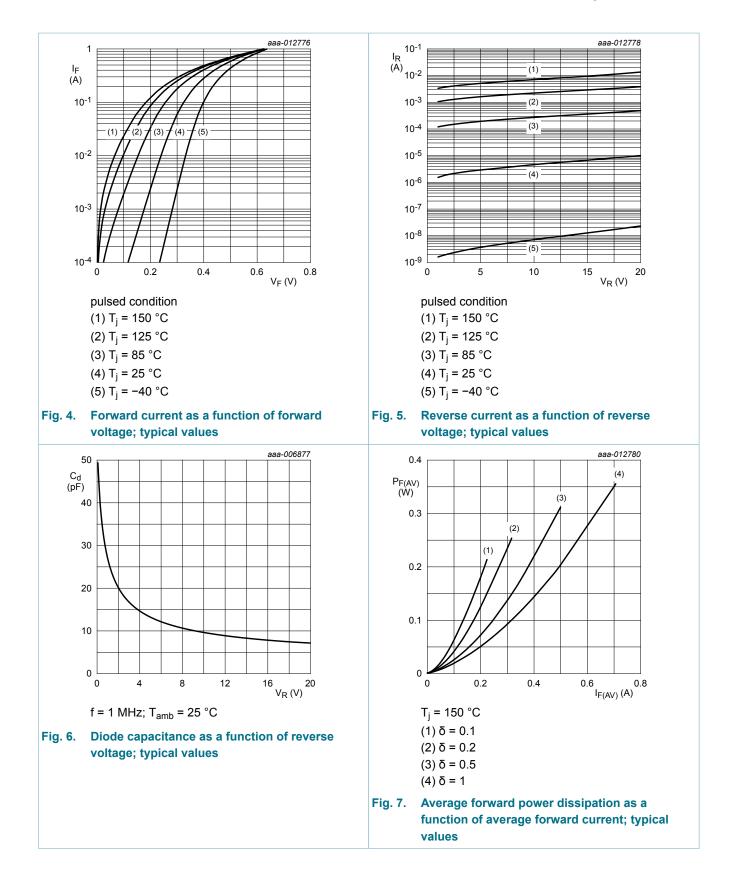
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## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)R</sub>	reverse breakdown voltage	I <sub>R</sub> = 100 μA; t <sub>p</sub> = 300 μs; δ = 0.02; T <sub>j</sub> = 25 °C	20	-	-	V
VF	forward voltage	I <sub>F</sub> = 0.1 mA; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C	-	120	180	mV
		$I_F$ = 1 mA; $t_p \le 300$ μs; δ ≤ 0.02; $T_j$ = 25 °C	-	180	250	mV
		I <sub>F</sub> = 10 mA; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C	-	245	310	mV
		$I_F$ = 100 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	330	380	mV
		I <sub>F</sub> = 200 mA; t <sub>p</sub> ≤ 300 μs; $\delta$ ≤ 0.02; T <sub>j</sub> = 25 °C	-	375	420	mV
		$I_F$ = 500 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>j</sub> = 25 °C	-	475	550	mV
I <sub>R</sub>	reverse current	$V_R$ = 6 V; $T_j$ = 25 °C; pulsed	-	3.2	-	μA
		$V_R$ = 10 V; $T_j$ = 25 °C; pulsed	-	5	25	μA
		$V_R$ = 20 V; $T_j$ = 25 °C; pulsed	-	10	45	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	25	-	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	10	-	pF
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 500 mA; I <sub>R</sub> = 500 mA; I <sub>R(meas)</sub> = 100 mA; T <sub>i</sub> = 25 °C	-	1.9	-	ns

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#### 20 V, 0.5 A low VF MEGA Schottky barrier rectifier

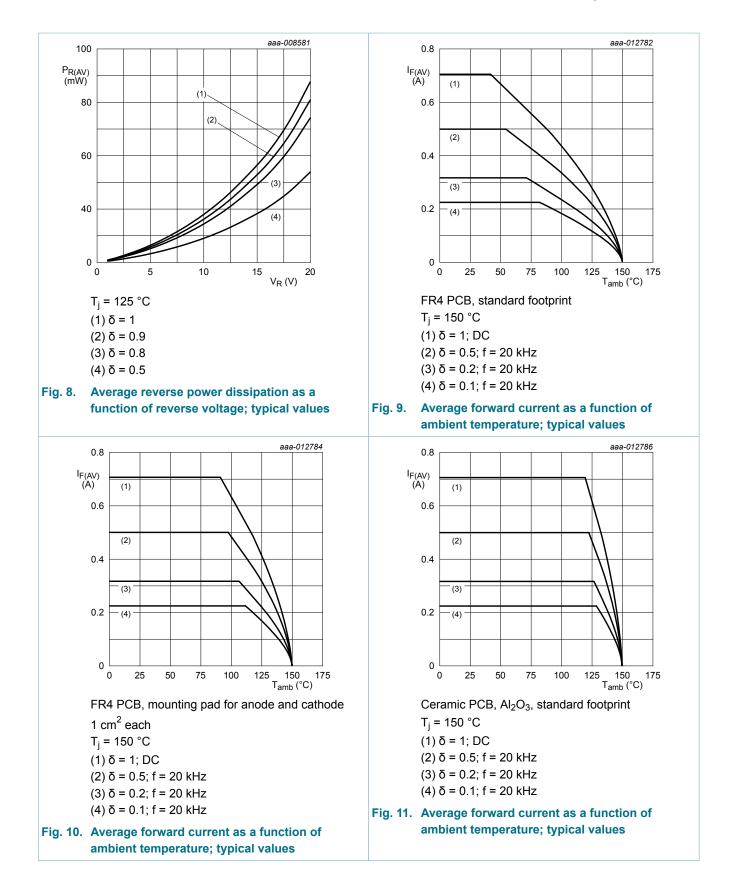


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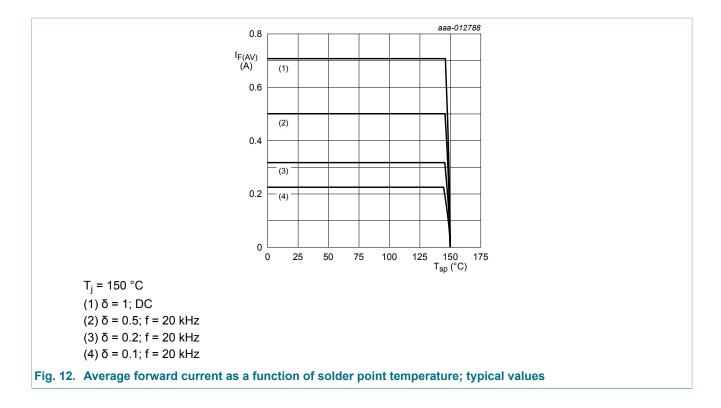
#### 20 V, 0.5 A low VF MEGA Schottky barrier rectifier



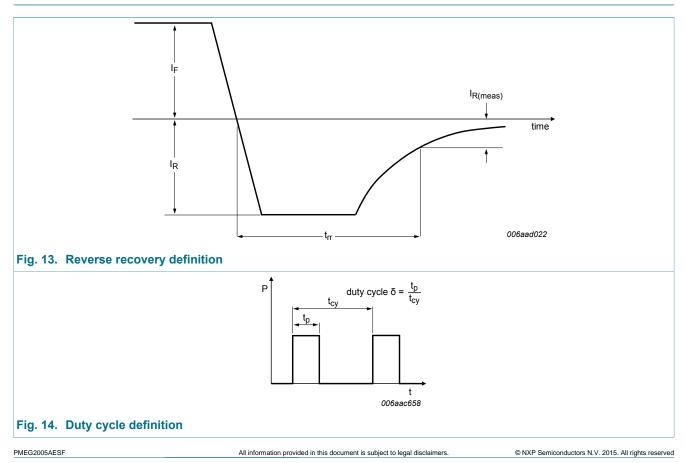
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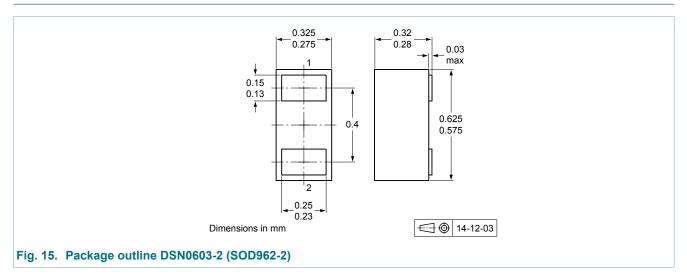
## 11. Test information



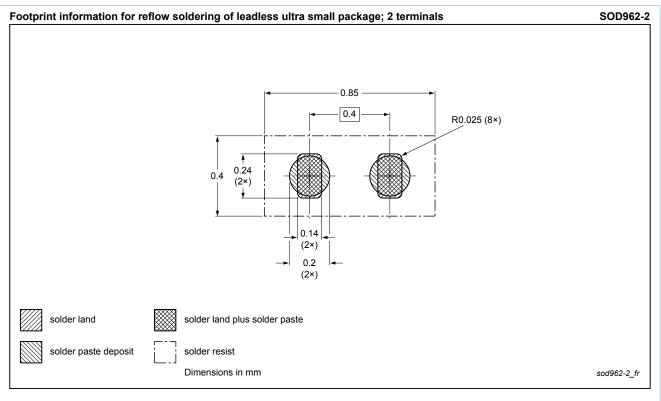
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The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

## 12. Package outline



## 13. Soldering



#### Fig. 16. Reflow soldering footprint for DSN0603-2 (SOD962-2)

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## 14. Revision history

Table 8.Revision history				
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG2005AESF v.2	20150213	Product data sheet	-	PMEG2005AESF v.1
Modifications:	Product sta	itus changed		
PMEG2005AESF v.1	20141219	Preliminary data sheet	-	-

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### 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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